

# 2SC3870

## Silicon NPN triple diffusion planar type

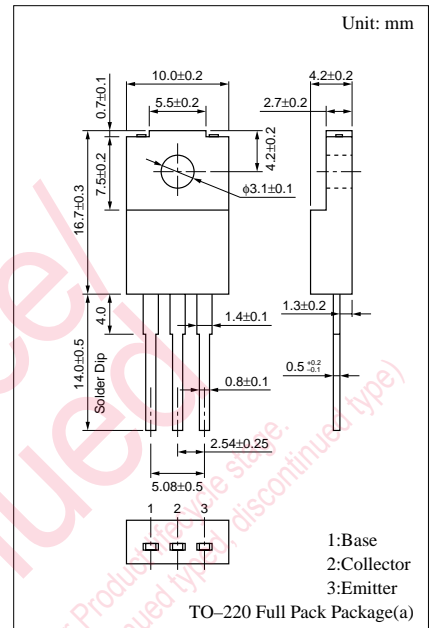
For high breakdown voltage high-speed switching

### ■ Features

- High-speed switching
- High collector to base voltage  $V_{CBO}$
- Wide area of safe operation (ASO)
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

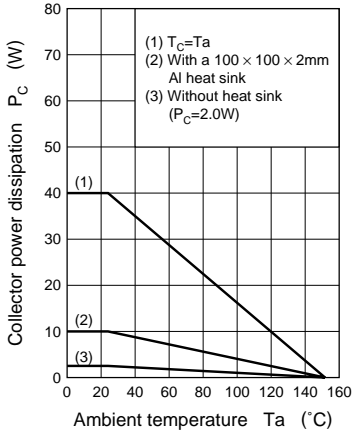
| Parameter                    | Symbol    | Ratings                | Unit             |   |
|------------------------------|-----------|------------------------|------------------|---|
| Collector to base voltage    | $V_{CBO}$ | 500                    | V                |   |
| Collector to emitter voltage | $V_{CES}$ | 500                    | V                |   |
|                              | $V_{CEO}$ | 400                    | V                |   |
| Emitter to base voltage      | $V_{EBO}$ | 7                      | V                |   |
| Peak collector current       | $I_{CP}$  | 15                     | A                |   |
| Collector current            | $I_C$     | 7                      | A                |   |
| Base current                 | $I_B$     | 3                      | A                |   |
| Collector power dissipation  | $P_C$     | $T_C=25^\circ\text{C}$ | 40               | W |
|                              |           | $T_a=25^\circ\text{C}$ | 2                |   |
| Junction temperature         | $T_j$     | 150                    | $^\circ\text{C}$ |   |
| Storage temperature          | $T_{stg}$ | -55 to +150            | $^\circ\text{C}$ |   |



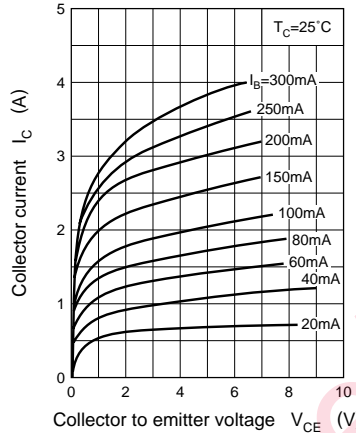
### ■ Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

| Parameter                               | Symbol        | Conditions   | min | typ | max | Unit          |
|---|---------------|--|-----|-----|-----|---------------|
| Collector cutoff current                | $I_{CBO}$     | $V_{CB} = 500\text{V}, I_E = 0$  |     |     | 100 | $\mu\text{A}$ |
| Emitter cutoff current                  | $I_{EBO}$     | $V_{EB} = 5\text{V}, I_C = 0$  |     |     | 100 | $\mu\text{A}$ |
| Collector to emitter voltage            | $V_{CEO}$     | $I_C = 10\text{mA}, I_B = 0$   | 400 |     |     | V             |
| Forward current transfer ratio          | $h_{FE1}$     | $V_{CE} = 5\text{V}, I_C = 0.1\text{A}$  | 15  |     |     |               |
|   | $h_{FE2}$     | $V_{CE} = 5\text{V}, I_C = 3\text{A}$  | 8   |     |     |               |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 3\text{A}, I_B = 0.6\text{A}$   |     |     | 1   | V             |
| Base to emitter saturation voltage      | $V_{BE(sat)}$ | $I_C = 3\text{A}, I_B = 0.6\text{A}$   |     |     | 1.5 | V             |
| Transition frequency                    | $f_T$         | $V_{CE} = 10\text{V}, I_C = 0.5\text{A}, f = 10\text{MHz}$                           |     | 30  |     | MHz           |
| Turn-on time                            | $t_{on}$      | $I_C = 3\text{A}, I_{B1} = 0.6\text{A}, I_{B2} = -1.2\text{A}, V_{CC} = 150\text{V}$ |     |     | 0.7 | $\mu\text{s}$ |
| Storage time                            | $t_{stg}$     |  |     |     | 2   | $\mu\text{s}$ |
| Fall time                               | $t_f$         |  |     |     | 0.3 | $\mu\text{s}$ |

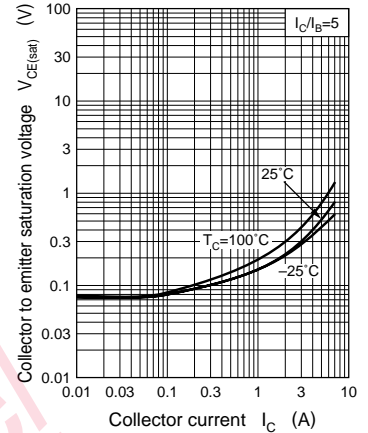
$P_C - T_a$



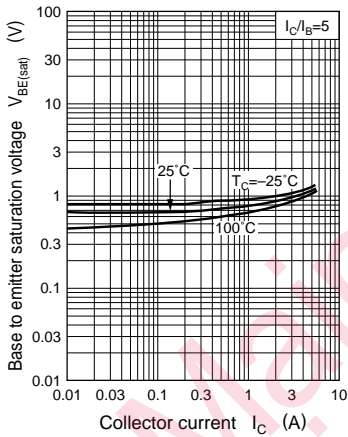
$I_C - V_{CE}$



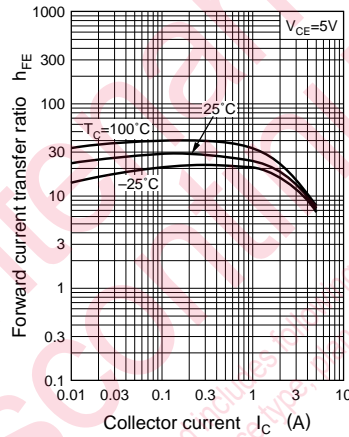
$V_{CE(sat)} - I_C$



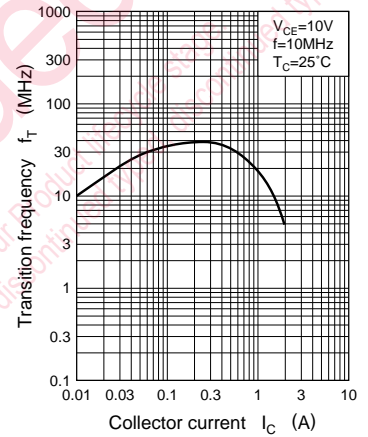
$V_{BE(sat)} - I_C$



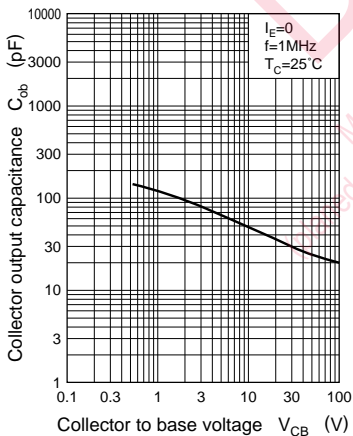
$h_{FE} - I_C$



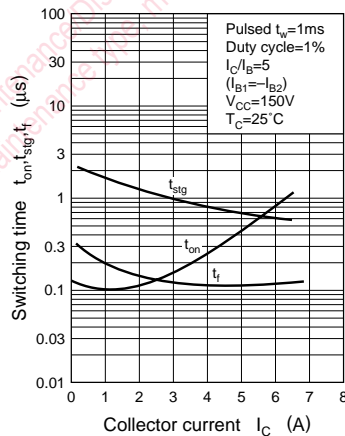
$f_T - I_C$



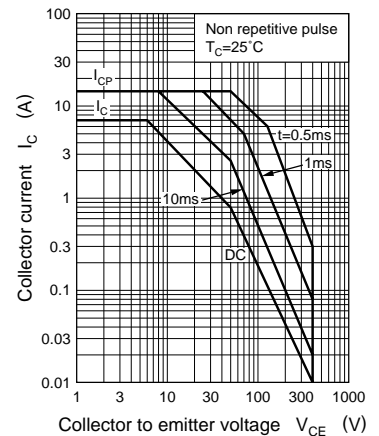
$C_{ob} - V_{CB}$



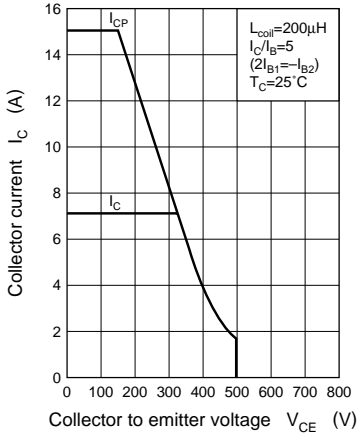
$t_{on}, t_{stg}, t_f - I_C$



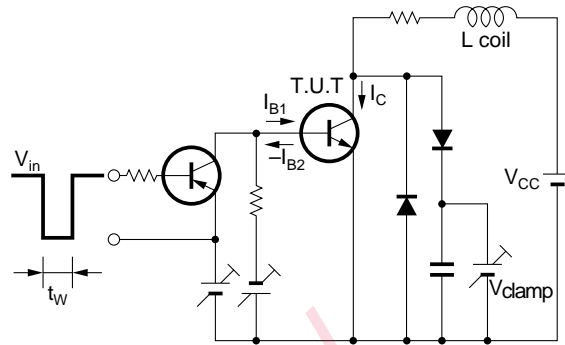
Area of safe operation (ASO)



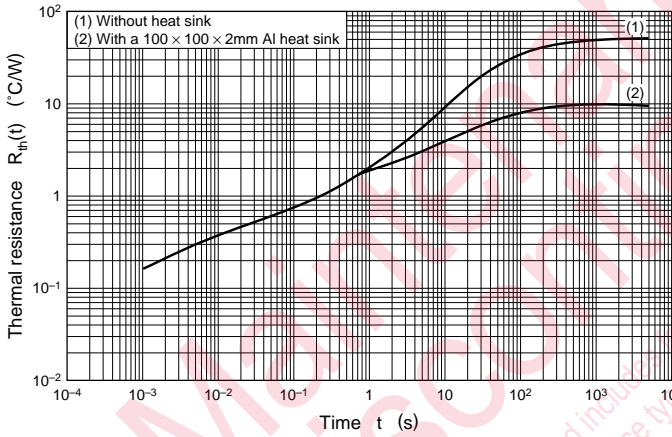
Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit



$R_{th}(t) - t$



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